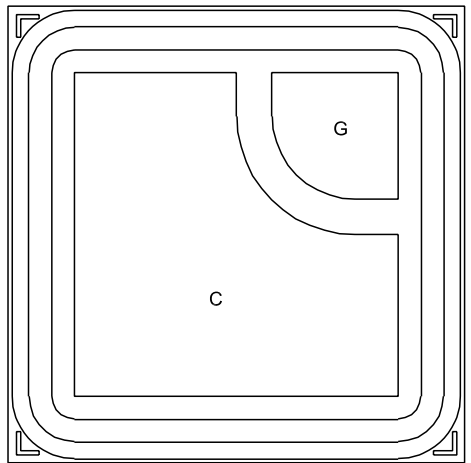


PROCESS DETAILS

Process	Glass Passivated Mesa
Die Size	110 x 110 MILS
Die Thickness	8.7 MILS
Cathode Bonding Pad Area	80 x 40 MILS
Gate Bonding Pad Area	31 x 31 MILS
Top Side Metalization	Al - 45,000Å
Back Side Metalization	Al/Mo/Ni/Ag - 32,000Å

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GEOMETRY



BACKSIDE ANODE R0

GROSS DIER PER 4 INCH WAFER

876

PRINCIPAL DEVICE TYPES

CS220-12M Series
CSDD-12M Series

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R0 (4- January 2006)